

**IN THE SPECIFICATION:**

**Please rewrite** the paragraph at page 4, lines 11-21, so that it reads as follows:

Referring to FIG. 1, adjacent transistors 2, 4 in a conventional CMOS device having a bulk silicon substrate 6 are mutually isolated from each other by a field oxide 8 formed by local oxidation of silicon (LOCOS) and by a channel stop 10 disposed below the field oxide 8. For n-channel transistors, the substrate 6 is lightly doped and the channel stop 10 is heavily doped with a p-type impurity. The sources and drains 12 of the transistors 2, 4 are heavily doped with an n-type impurity, except for parts extending under the gate electrode 14, which are lightly doped with the n-type impurity.